

**Table 1: General Features**

TYPE	V <sub>CES</sub>	V <sub>CE(sat)</sub> (Max) @25°C	I <sub>C</sub> @100°C
STGB5NC60KD	600 V	< 2.5 V	10 A
STGF5NC60KD	600 V	< 2.5 V	10 A
STGP5NC60KD	600 V	< 2.5 V	10 A

- OFF LOSSES INCLUDE TAIL CURRENT
- LOW ON-VOLTAGE DROP (V<sub>cesat</sub>)
- SHORT CIRCUIT RATED
- SWITCHING LOSSES INCLUDE DIODE RECOVERY ENERGY
- LOWER C<sub>RES</sub> / C<sub>IES</sub> RATIO

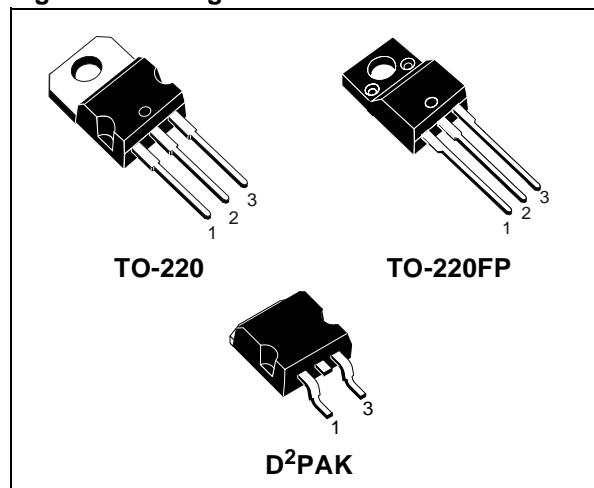
### DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency motor control applications with short circuit withstand capability.

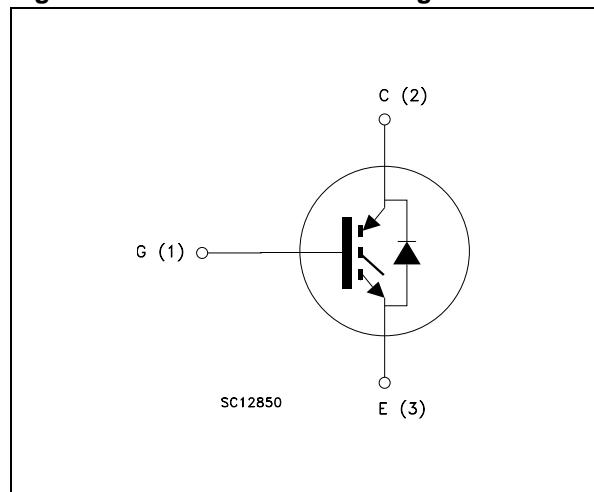
### APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS and PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES
- MOTOR DRIVERS

**Figure 1: Package**



**Figure 2: Internal Schematic Diagram**



**Table 2: Order Codes**

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGB5NC60KDT4	GB5NC60KD	D <sup>2</sup> PAK	TAPE & REEL
STGF5NC60KD	GF5NC60KD	TO-220FP	TUBE
STGP5NC60KD	GP5NC60KD	TO-220	TUBE

**Table 3: Absolute Maximum ratings**

Symbol	Parameter	Value		Unit
		STGB5NC60KD STGP5NC60KD	STGF5NC60KD	
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>GS</sub> = 0)	600		V
V <sub>ECR</sub>	Emitter-Collector Voltage	20		V
V <sub>GE</sub>	Gate-Emitter Voltage	±20		V
I <sub>c</sub>	Collector Current (continuous) at T <sub>C</sub> = 25°C (#)	20		A
I <sub>c</sub>	Collector Current (continuous) at T <sub>C</sub> = 100°C (#)	10		A
I <sub>CM</sub> (■)	Collector Current (pulsed)	40		A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	60	25	W
	Derating Factor	0.48	0.20	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage A.C.(t = 1 sec; T <sub>c</sub> = 25°C)	--	2500	V
T <sub>stg</sub>	Storage Temperature	– 55 to 150		°C
T <sub>j</sub>	Operating Junction Temperature			°C

(■)Pulse width limited by max. junction temperature.

**Table 4: Thermal Data**

			Min.	Typ.	Max.	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	TO-220 D2PAK			2.08	°C/W
		TO-220FP			5.0	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient				62.5	°C/W
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose (1.6 mm from case, for 10 sec.)			300		°C

### ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> =25°C UNLESS OTHERWISE SPECIFIED)

**Table 5: Main Parameters**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>BR(CES)</sub>	Collector-Emitter Breakdown Voltage	I <sub>c</sub> = 250 µA, V <sub>GE</sub> = 0	600			V
I <sub>CES</sub>	Collector cut-off Current (V <sub>GE</sub> = 0)	V <sub>CE</sub> = Max Rating, T <sub>C</sub> = 25°C V <sub>CE</sub> =Max Rating, T <sub>c</sub> = 125°C			250 2	µA mA
I <sub>GES</sub>	Gate-Emitter Leakage Current (V <sub>CE</sub> = 0)	V <sub>GE</sub> = ±20V , V <sub>CE</sub> = 0			±250	nA
V <sub>GE(th)</sub>	Gate Threshold Voltage	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>c</sub> = 250 µA	5		7	V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15V, I <sub>c</sub> = 5A V <sub>GE</sub> = 15V, I <sub>c</sub> = 5A, T <sub>c</sub> = 125°C		2 1.8	2.5	V V

(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

**ELECTRICAL CHARACTERISTICS (CONTINUED)****Table 6: Dynamic**

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Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}(1)$	Forward Transconductance	$V_{CE} = 15 \text{ V}$ , $I_C = 5 \text{ A}$		15		S
$C_{ies}$ $C_{oes}$ $C_{res}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25 \text{ V}$ , $f = 1 \text{ MHz}$ , $V_{GE} = 0$		410 48 9		pF pF pF
$Q_g$ $Q_{ge}$ $Q_{gc}$	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 390 \text{ V}$ , $I_C = 5 \text{ A}$ , $V_{GE} = 15 \text{ V}$ , (see Figure 5)		19 TBD TBD		nC nC nC
$t_{scw}$	Short Circuit Withstand Time	$V_{CE} = 0.5 \text{ V}_{BR(CES)}$ , $T_j = 125^\circ\text{C}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$	TBD			$\mu\text{s}$

(1) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%**Table 7: Switching On**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$ ( $d/dt$ ) <sub>on</sub> Eon (2)	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 390 \text{ V}$ , $I_C = 5 \text{ A}$ $R_G = 3.3 \Omega$ , $V_{GE} = 15 \text{ V}$ , $T_j = 25^\circ\text{C}$ (see Figure 3)		TBD TBD TBD TBD		ns ns A/ $\mu\text{s}$ $\mu\text{J}$
$t_{d(on)}$ $t_r$ ( $d/dt$ ) <sub>on</sub> Eon (2)	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 390 \text{ V}$ , $I_C = 5 \text{ A}$ $R_G = 3.3 \Omega$ , $V_{GE} = 15 \text{ V}$ , $T_j = 125^\circ\text{C}$ (see Figure 3)		TBD TBD TBD TBD		ns ns A/ $\mu\text{s}$ $\mu\text{J}$

2) Eon is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs & DIODE are at the same temperature ( $25^\circ\text{C}$  and  $125^\circ\text{C}$ )**Table 8: Switching Off**

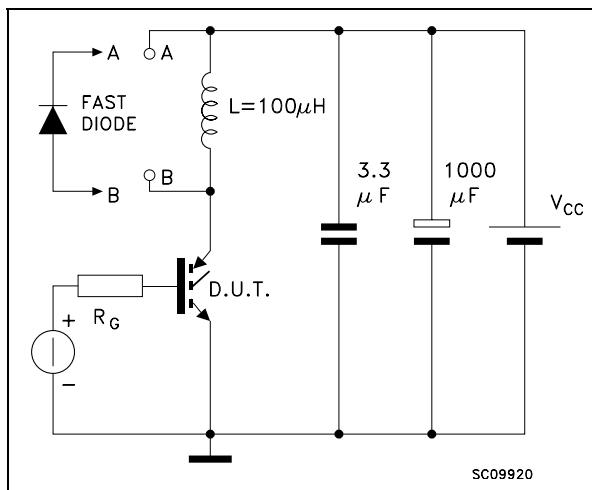
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$ $t_d(off)$ $t_f$ E <sub>off</sub> (3) E <sub>ts</sub>	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	$V_{cc} = 390 \text{ V}$ , $I_C = 5 \text{ A}$ , $R_{GE} = 3.3 \Omega$ , $V_{GE} = 15 \text{ V}$ $T_j = 25^\circ\text{C}$ (see Figure 3)		TBD TBD 75 TBD TBD		ns ns ns $\mu\text{J}$ $\mu\text{J}$
$t_r(V_{off})$ $t_d(off)$ $t_f$ E <sub>off</sub> (3) E <sub>ts</sub>	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	$V_{cc} = 390 \text{ V}$ , $I_C = 5 \text{ A}$ , $R_{GE} = 3.3 \Omega$ , $V_{GE} = 15 \text{ V}$ $T_j = 125^\circ\text{C}$ (see Figure 3)		TBD TBD 110 TBD TBD		ns ns ns $\mu\text{J}$ $\mu\text{J}$

(3) Turn-off losses include also the tail of the collector current.

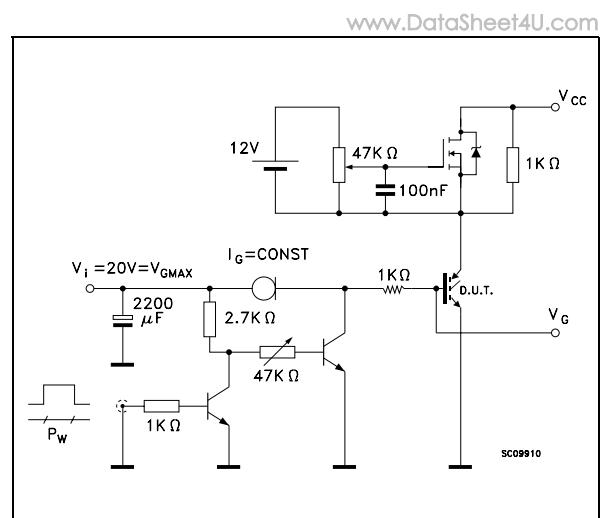
**Table 9: Collector-Emitter Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_f$ $I_{fm}$	Forward Current Forward Current Pulsed				7.5 12	A A
$V_f$	Forward On-Voltage	$I_f = 1.5 \text{ A}$ $I_f = 1.5 \text{ A}, T_j = 125 \text{ }^\circ\text{C}$		1.6 1.3	2.9	V V
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 1.5 \text{ A}, V_R = 30 \text{ V},$ $T_j = 25^\circ\text{C}, di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 6)		TBD TBD TBD		ns nC A
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 1.5 \text{ A}, V_R = 30 \text{ V},$ $T_j = 125^\circ\text{C}, di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 6)		TBD TBD TBD		ns nC A

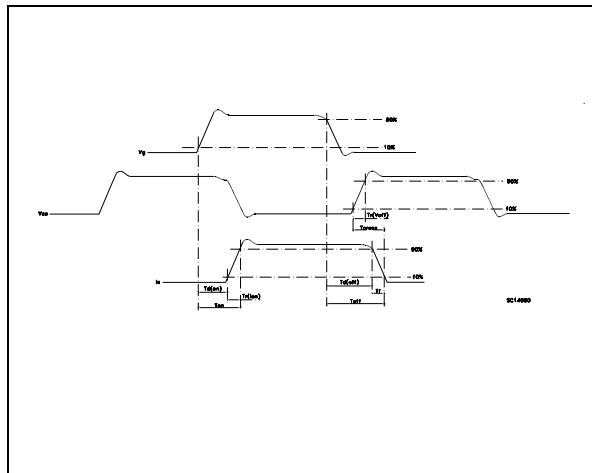
**Figure 3: Test Circuit for Inductive Load Switching**



**Figure 5: Gate Charge Test Circuit**

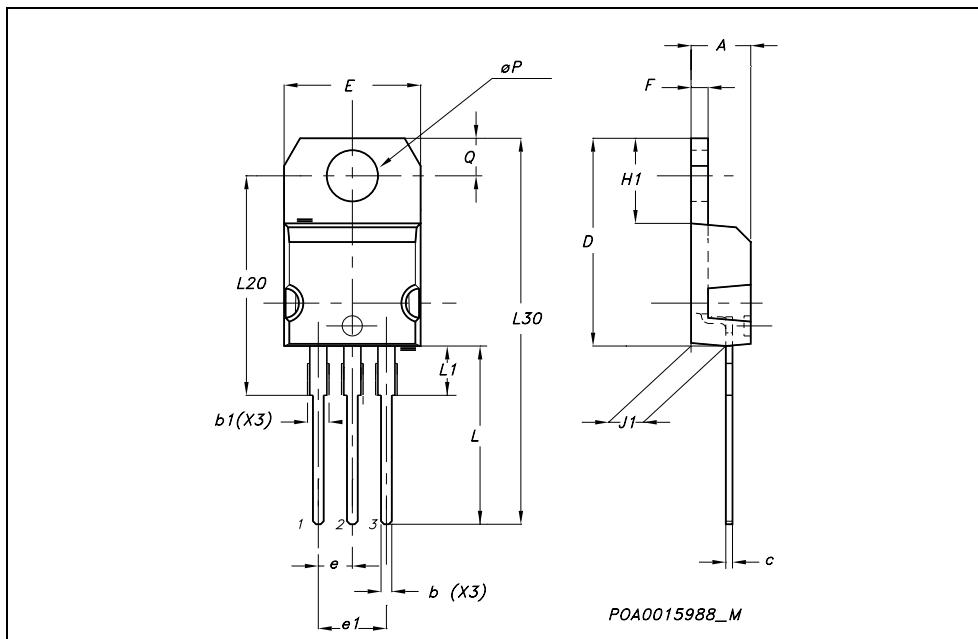


**Figure 4: Switching Waveforms**



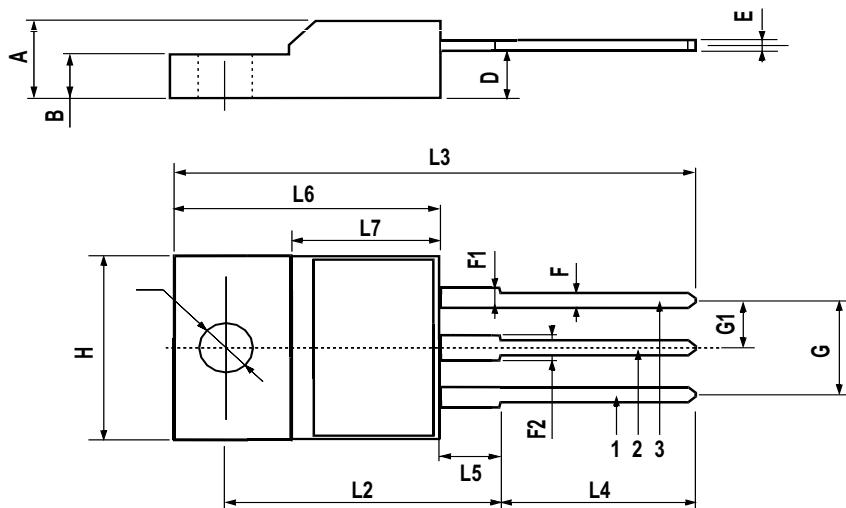
## TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
$\phi P$	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



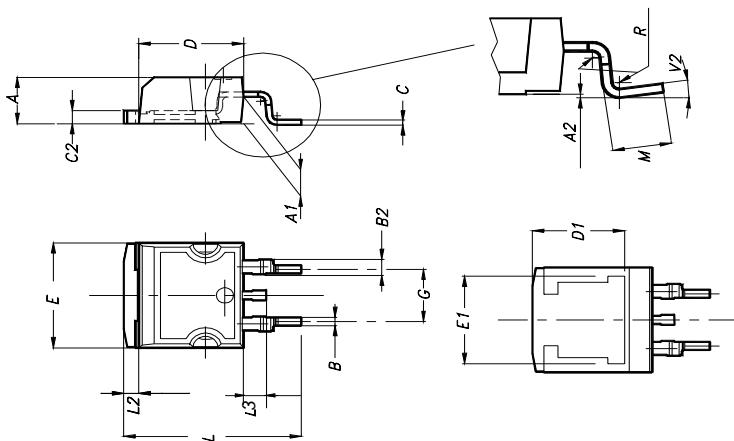
## TO-220FP MECHANICAL DATA

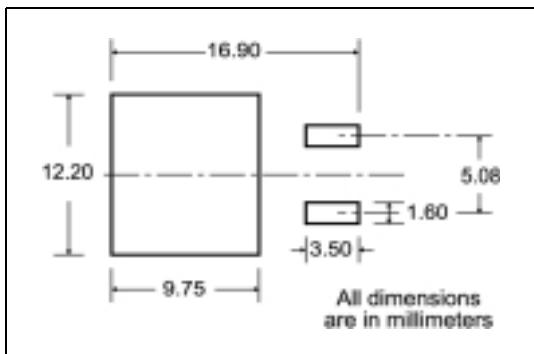
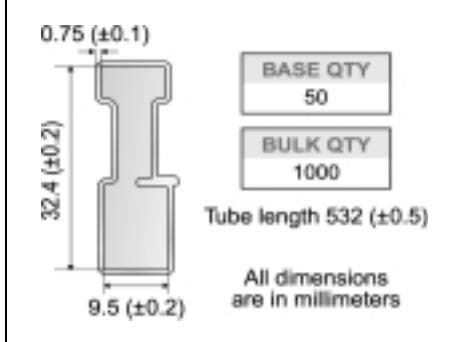
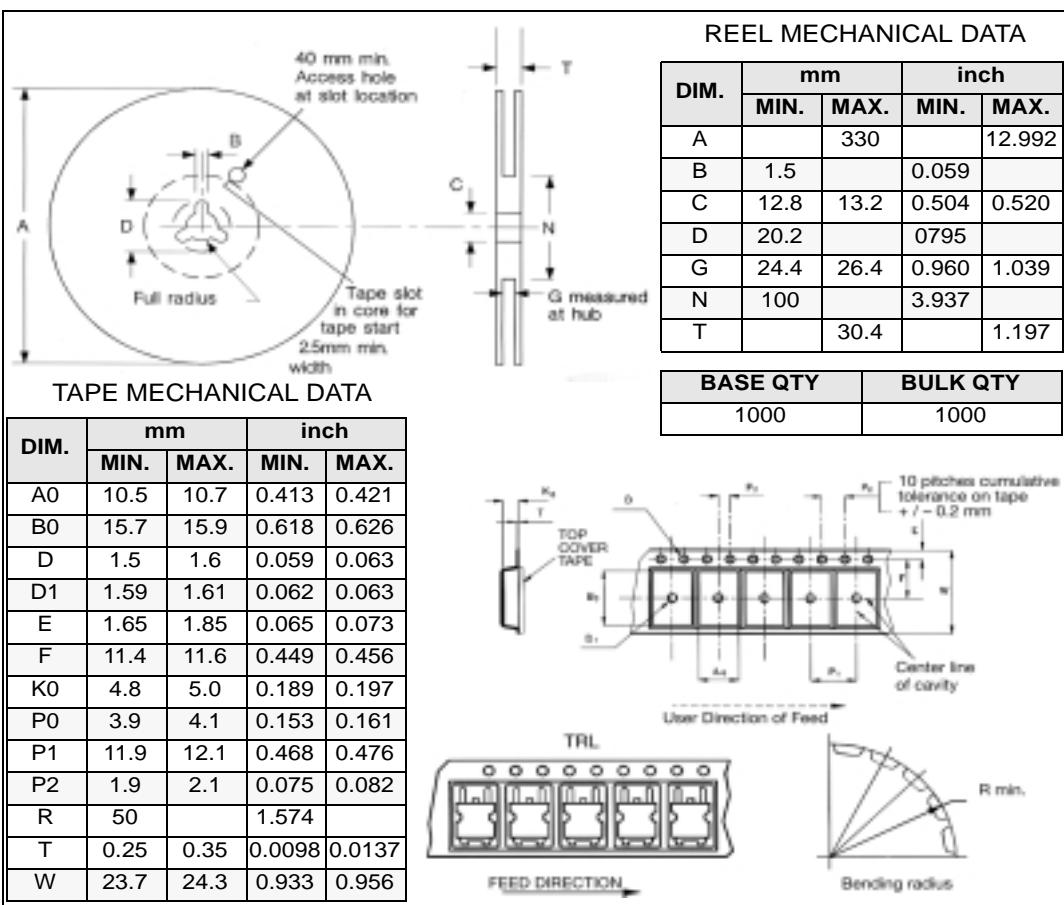
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



**D<sup>2</sup>PAK FOOTPRINT****TUBE SHIPMENT (no suffix)\*****TAPE AND REEL SHIPMENT (suffix "T4")\***

\* on sales type

**Table 10: Revision History**

Date	Revision	Description of Changes	www.DataSheet4U.com
14-Feb-2005	1	New release	

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